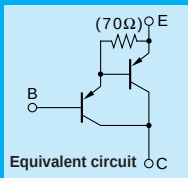
Darlington 2SB1625



Silicon PNP Epitaxial Planar Transistor (Complement to type 2SD2494)

Application : Audio, Series Regulator and General Purpose

Absolute maximum ratings (Ta=25°C)

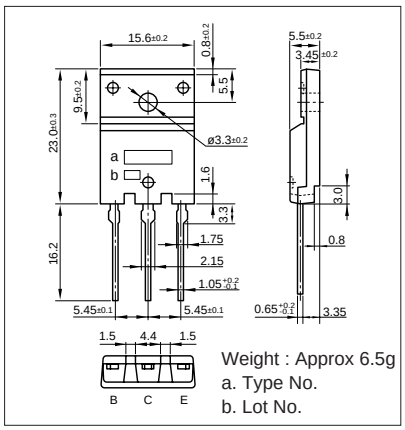
Symbol	2SB1625	Unit
V_{CBO}	–110	V
V_{CEO}	–110	V
V_{EBO}	–5	V
I_C	–6	A
I_B	–1	A
P_C	60(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SB1625	Unit
I_{CBO}	V_{CB}=–110V	–100max	μA
I_{EBO}	V_{EB}=–5V	–100max	μA
$V_{(BR)CEO}$	I_C=–30mA	–110min	V
h_{FE}	V_{CE}=–4V, I_C=–5A	5000min*	
$V_{CE(sat)}$	I_C=–5A, I_B=–5mA	–2.5max	V
$V_{BE(sat)}$	I_C=–5A, I_B=–5mA	–3.0max	V
f_T	V_{CE}=–12V, I_E=0.5A	–100typ	MHz
C_{OB}	V_{CB}=–10V, f=1MHz	–110typ	pF

*h_{FE} Rank O(5000 to 12000), P(6500 to 20000), Y(15000 to 30000)

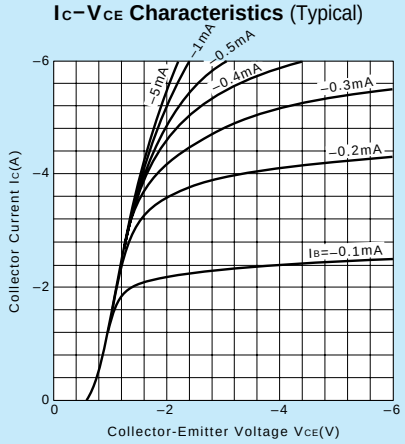
External Dimensions FM100(TO3P)



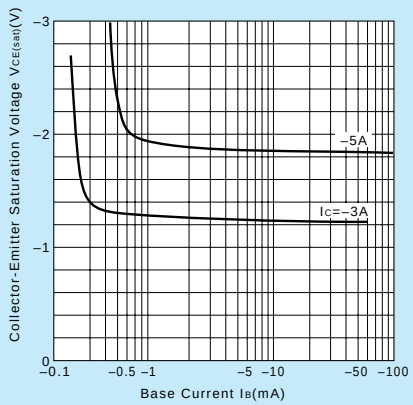
Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (mA)	I_{B2} (mA)	ton (μs)	tstg (μs)	tf (μs)
–30	6	–5	–10	5	–5	5	1.1typ	3.2typ	1.1typ

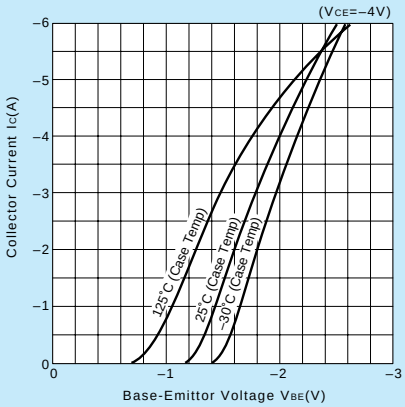
I_C–V_{CE} Characteristics (Typical)



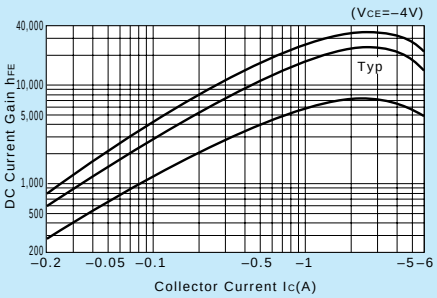
$V_{CE(sat)}$–I_B Characteristics (Typical)



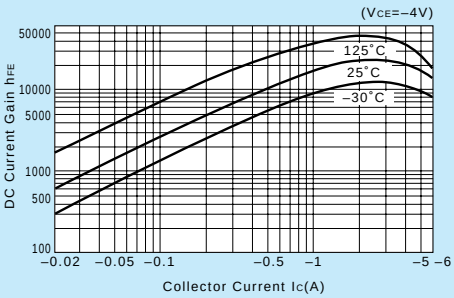
I_C–V_{BE} Temperature Characteristics (Typical)



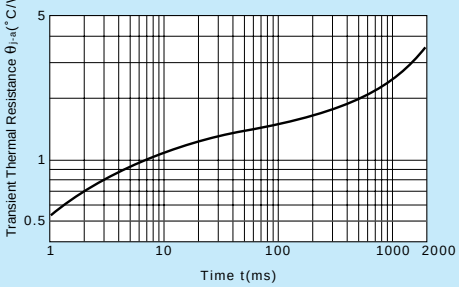
h_{FE}–I_C Characteristics (Typical)



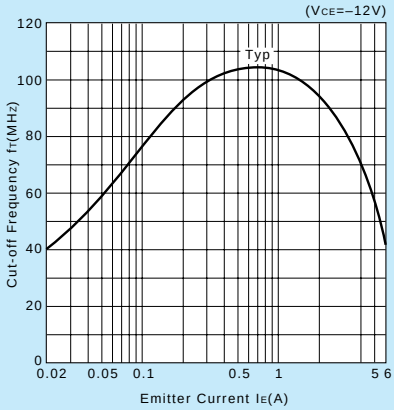
h_{FE}–I_C Temperature Characteristics (Typical)



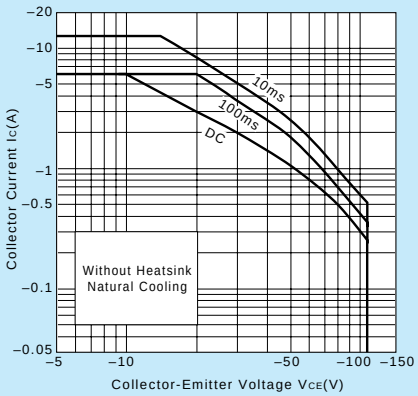
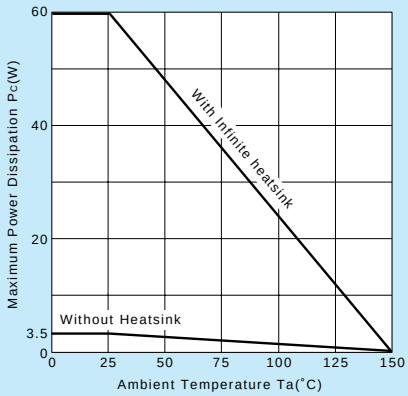
$\theta_{j\text{-}a}$–t Characteristics



f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc–Ta Derating